

CLAIM

What is claimed is:

1. An improved processing method for the packaging technique of a large size FED comprising the steps of:
 - 5 providing an ITO conducting glass;
 - forming a BM layer area, a multi-phosphor layer area and a hollow area on an ITO conducting glass using the first screen mask and the second screen mask, and forming a Cr/CrO_x layer area in the hollow area;
 - 10 forming an Al layer on said areas, then carrying out a sintering process of phosphor layer to form an AlO_x layer;
 - fixing a spacer on the hollow area of the AlO_x layer; and
 - aligning process for a lower plate.
2. An improved packaging technique of a large size FED of claim 1, wherein the method of forming an Al layer is an evaporation, the thickness is about 1000-3000 angstroms.
3. An improved packaging technique of a large size FED of claim 1, wherein the temperatures of the sintering process of the phosphor layer is about 500-560 °C.
- 20 4. An improved packaging technique of a large size FED of claim 1, wherein the thickness of the AlO_x layer is around 50-200 angstroms.
5. An improved packaging technique of a large size FED of claim 1, wherein the thickness of the Cr/CrO_x layer is around 1000-3000 angstroms.

6. An improved packaging technique of a large size FED of claim 1, wherein the spacer is form as a column structure, and the height of the spacer is about 1.1 mm.

7. An improved packaging technique of a large size FED of claim 5 1, wherein there is a plurality of bonding areas between the spacer and the AlO_x layer.

8. An improved packaging technique of a large size FED of claim 1, wherein said method of fixing the spacer is an anodic bonding technique.

10 9. An improved packaging technique of a large size FED of claim 1, wherein the voltage of fixing the spacer is 1.00-1.50 V/ μm .

10. An improved packaging technique of a large size FED of claim 1, wherein the temperature of fixing the substrate glass of the spacer is 200-300 °C.

15 11. An improved structure for the packaging technique of a large size FED comprising of:

- an ITO conducting glass;
- on the ITO conducting glass is defined to a BM layer area, a multi-phosphor layer area, and a hollow area, in which the inside of 20 a hollow area is formed a Cr/CrO_x layer area;
- said areas are coated with an Al layer;
- an Al layer is coated with an AlO_x layer;
- a spacer is fixed on an AlO_x layer of the hollow area; and
- a lower plate is fixed on the spacer.

25 12. An improved packaging technique of a large size FED of

claim11, wherein said method of forming an Al layer is an evaporation, and the thickness is around 1000-3000 angstroms.

13. An improved packaging technique of a large size FED of claim11, wherein the temperature of the sintering process of the
5 phosphor layer is around 500-560 °C.

14. An improved packaging technique of a large size FED of claim 11, wherein the thickness of the AlO_x layer is around 50-200 angstroms.

15. An improved packaging technique of a large size FED of claim
10 11, wherein said the thickness of the Cr/CrO_x layer is around 1000-3000 angstroms.

16. An improved packaging technique of a large size FED of claim 11, wherein said spacer is form as a column structure, and the height of the spacer is about 1.1 mm.

15 17. An improved packaging technique of a large size FED of claim 11, wherein there is a plurality of bonding areas between the spacer and an AlO_x layer.

18. An improved packaging technique of a large size FED of claim 11, wherein said method of fixing the spacer is an anodic bonding
20 technique.

19. An improved packaging technique of a large size FED of claim 11, wherein the voltage of fixing the spacer is 1.00-1.50 V/ μm .

20. An improved packaging technique of a large size FED of claim 11, wherein the temperature of fixing the substrate glass of the
25 spacer is 200-300 °C.